

Silicon Carbide (SiC) MOSFET – 80 mohm, 1200 V, M1, D2PAK-7L

NVBG080N120SC1

Features

- Typ. $R_{DS(on)} = 80 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_{G(\text{tot})} = 56 \text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss} = 79 \text{ pF}$)
- 100% Avalanche Tested
- AEC-Q101 Qualified and PPAP Capable
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

Typical Applications

- Automotive On Board Charger
- Automotive DC-DC Converter for EV/HEV

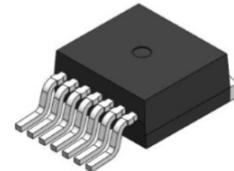
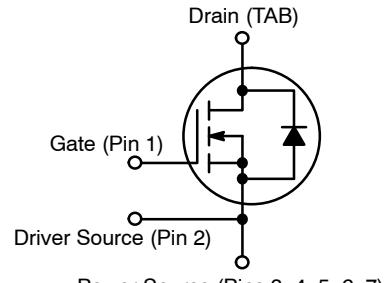
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	1200	V	
Gate-to-Source Voltage		V_{GS}	-15/+25	V	
Recommended Operation Values of Gate-Source Voltage		V_{GSop}	-5/+20	V	
Continuous Drain Current (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	I_D	30	A
Power Dissipation (Note 1)		$T_C = 25^\circ\text{C}$	P_D	179	W
Continuous Drain Current (Note 1)	Steady State	$T_C = 100^\circ\text{C}$	I_D	21	A
Power Dissipation (Note 1)		$T_C = 100^\circ\text{C}$	P_D	89	W
Pulsed Drain Current (Note 2)	$T_C = 25^\circ\text{C}$	I_{DM}	110	A	
Single Pulse Surge Drain Current Capability	$T_C = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$, $R_G = 4.7 \Omega$	I_{DSC}	132	A	
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to +175	°C	
Source Current (Body Diode)		I_S	18	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_L = 18.5 \text{ A}_{pk}$, $L = 1 \text{ mH}$) (Note 3)		E_{AS}	171	mJ	
Maximum Lead Temperature for Soldering, 1/8" from Case for 10 Seconds		T_L	300	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

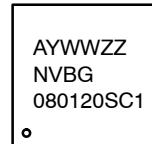
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. E_{AS} of 171 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 1 \text{ mH}$, $I_{AS} = 18.5 \text{ A}$, $V_{DD} = 120 \text{ V}$, $V_{GS} = 18 \text{ V}$.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
1200 V	110 mΩ @ 20 V	30 A



D2PAK-7L
CASE 418BJ

MARKING DIAGRAM



A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Lot Traceability
 NVBG080120SC1 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NVBG080N120SC1	D2PAK-7L	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

NVBG080N120SC1

Table 1. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-to-Case (Note 1)	$R_{\theta JC}$	0.84	°C/W
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	40	°C/W

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 1 \text{ mA}$		1200		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}/T_J}$	$I_D = 1 \text{ mA}$, refer to 25°C			0.5	$^\circ\text{C}/\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}$,	$T_J = 25^\circ\text{C}$		100	μA
		$V_{\text{DS}} = 1200 \text{ V}$	$T_J = 175^\circ\text{C}$		1	mA
Gate-to-Source Leakage Current	I_{GSS}	$V_{\text{GS}} = +25/-15 \text{ V}, V_{\text{DS}} = 0 \text{ V}$			± 1	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}, I_D = 5 \text{ mA}$	1.8	3	4.3	V
Recommended Gate Voltage	V_{GOP}		-5		+20	V
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 20 \text{ V}, I_D = 20 \text{ A}, T_J = 25^\circ\text{C}$		80	110	$\text{m}\Omega$
		$V_{\text{GS}} = 20 \text{ V}, I_D = 20 \text{ A}, T_J = 150^\circ\text{C}$		121		$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 20 \text{ V}, I_D = 20 \text{ A}$		11		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}, V_{\text{DS}} = 800 \text{ V}$		1154		pF
Output Capacitance	C_{OSS}			79		
Reverse Transfer Capacitance	C_{RSS}			7.9		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = -5/20 \text{ V}, V_{\text{DS}} = 600 \text{ V}, I_D = 20 \text{ A}$		56		nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$			10		
Gate-to-Source Charge	Q_{GS}			18		
Gate-to-Drain Charge	Q_{GD}			11		
Gate-Resistance	R_{G}		$f = 1 \text{ MHz}$		1.2	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = -5/20 \text{ V}, V_{\text{DS}} = 800 \text{ V}, I_D = 20 \text{ A}, R_{\text{G}} = 4.7 \Omega, \text{Inductive Load}$		12	22	ns
Rise Time	t_r			12	22	
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			21	34	
Fall Time	t_f			9	18	
Turn-On Switching Loss	E_{ON}			135		
Turn-Off Switching Loss	E_{OFF}			46		μJ
Total Switching Loss	E_{TOT}			181		

DRAIN-SOURCE DIODE CHARACTERISTICS

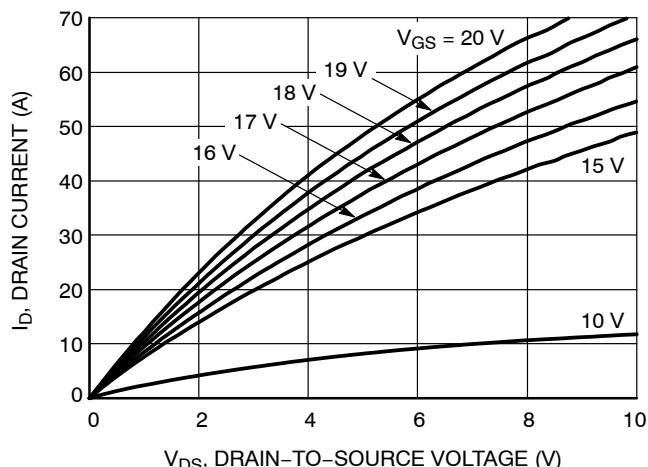
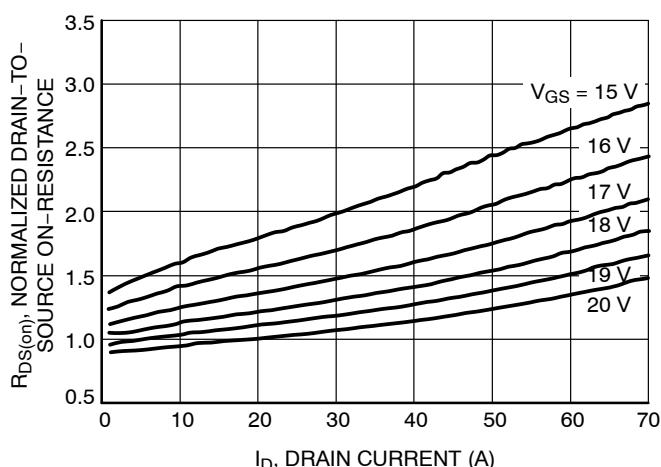
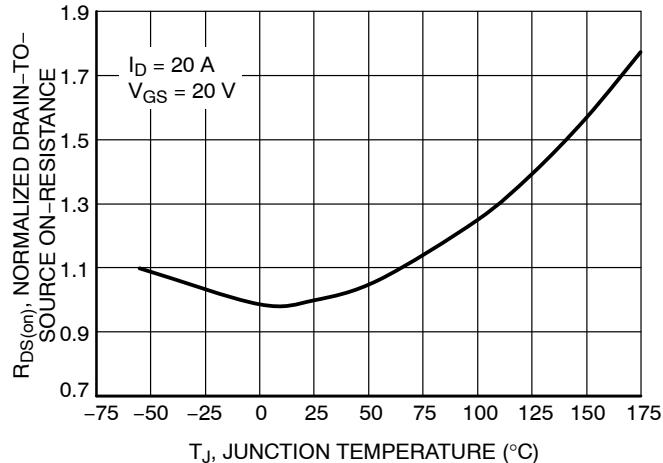
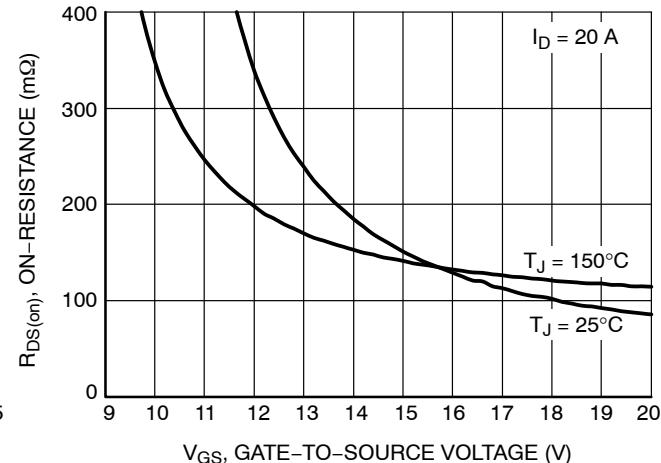
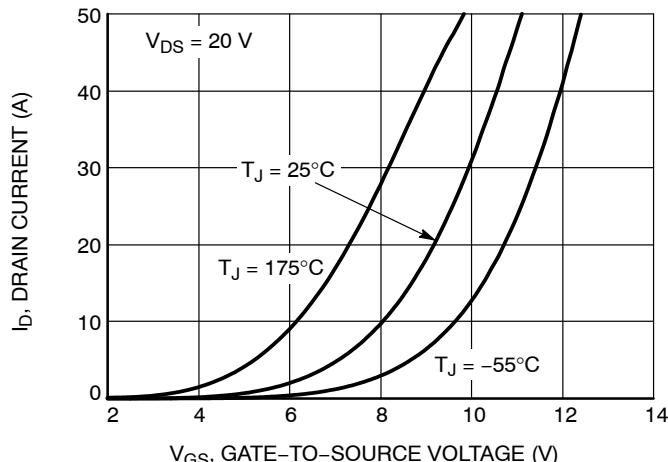
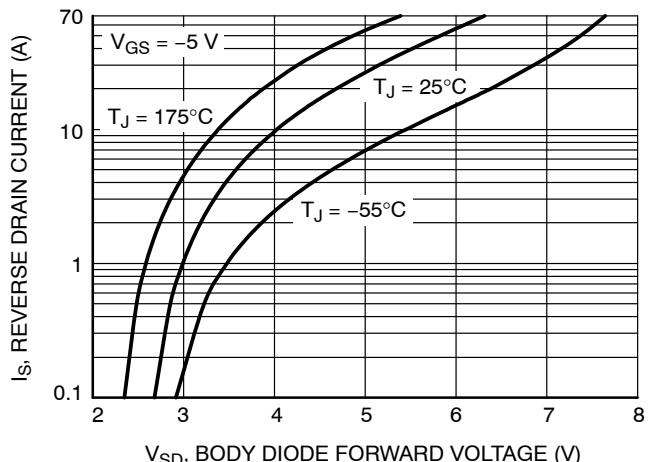
Continuous Drain-Source Diode Forward Current	I_{SD}	$V_{\text{GS}} = -5 \text{ V}, T_J = 25^\circ\text{C}$		18	A
Pulsed Drain-Source Diode Forward Current (Note 2)	I_{SDM}	$V_{\text{GS}} = -5 \text{ V}, T_J = 25^\circ\text{C}$		110	A
Forward Diode Voltage	V_{SD}	$V_{\text{GS}} = -5 \text{ V}, I_{\text{SD}} = 10 \text{ A}, T_J = 25^\circ\text{C}$		3.9	V

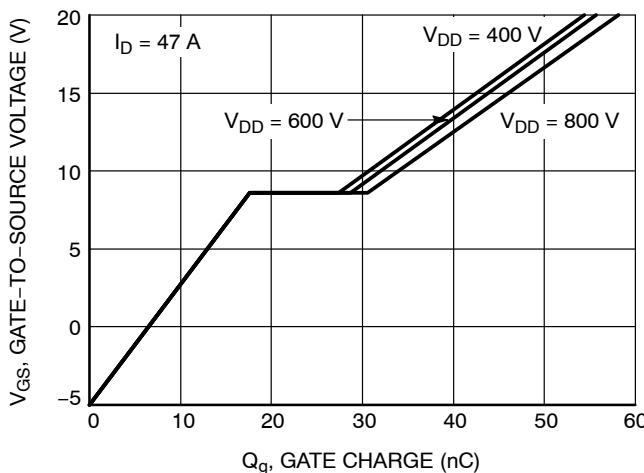
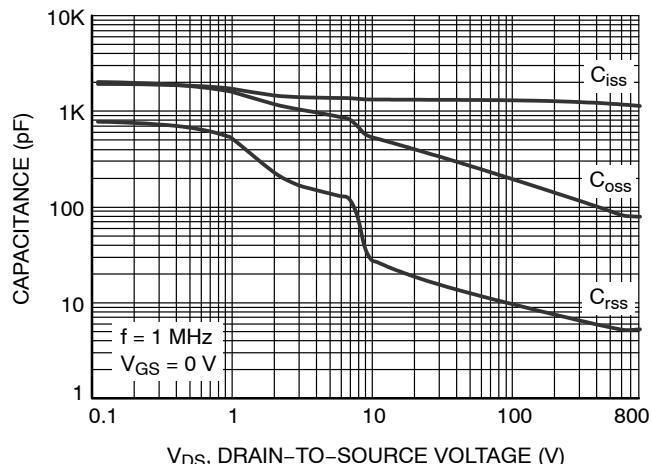
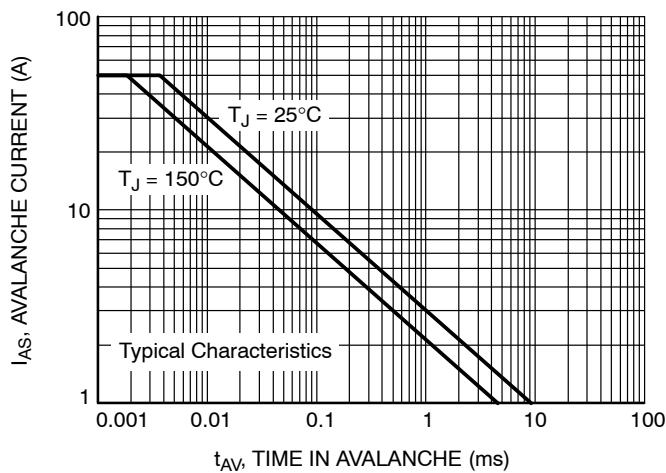
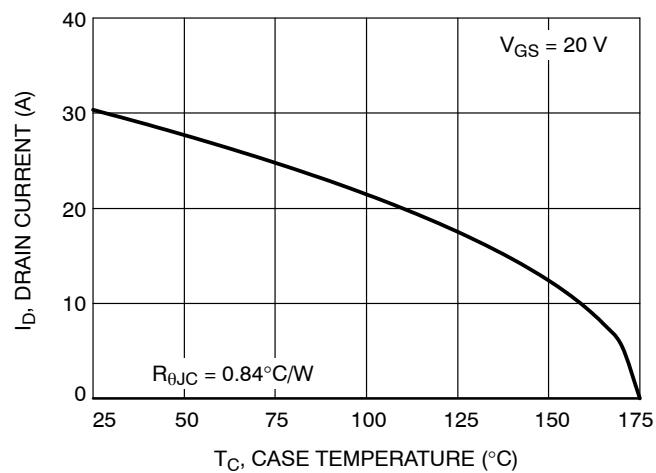
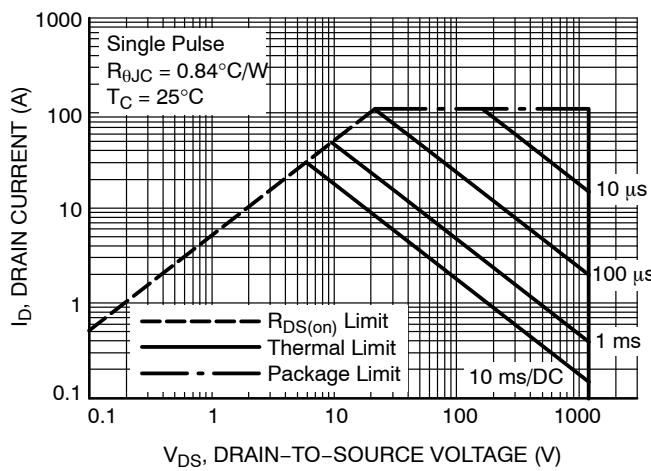
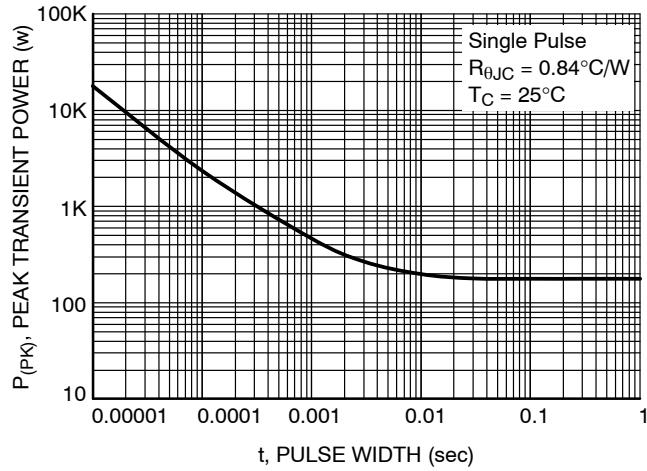
NVBG080N120SC1

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS						
Reverse Recovery Time	t_{RR}	$V_{GS} = -5/20 \text{ V}$, $I_{SD} = 20 \text{ A}$, $dI_S/dt = 1000 \text{ A}/\mu\text{s}$		16.2		ns
Reverse Recovery Charge	Q_{RR}			61.6		nC
Reverse Recovery Energy	E_{REC}			4.1		μJ
Peak Reverse Recovery Current	I_{RRM}			7.6		A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

Figure 3. On-Resistance Variation with Temperature

Figure 4. On-Resistance vs. Gate-to-Source Voltage

Figure 5. Transfer Characteristics

Figure 6. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS (continued)

Figure 7. Gate-to-Source Voltage vs. Total Charge

Figure 8. Capacitance vs. Drain-to-Source Voltage

Figure 9. Unclamped Inductive Switching Capability

Figure 10. Maximum Continuous Drain Current vs. Case Temperature

Figure 11. Safe Operating Area

Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (continued)

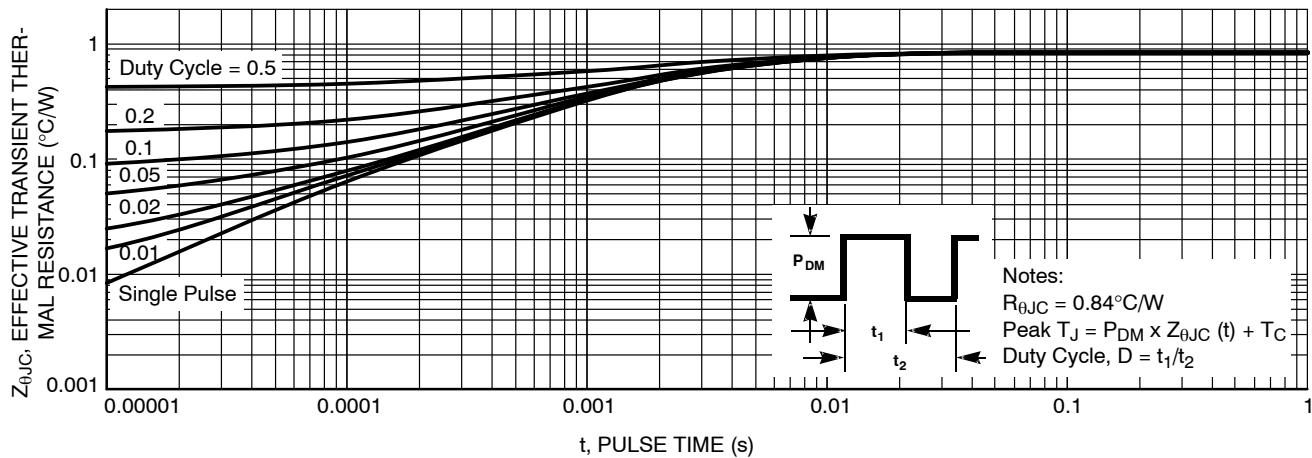
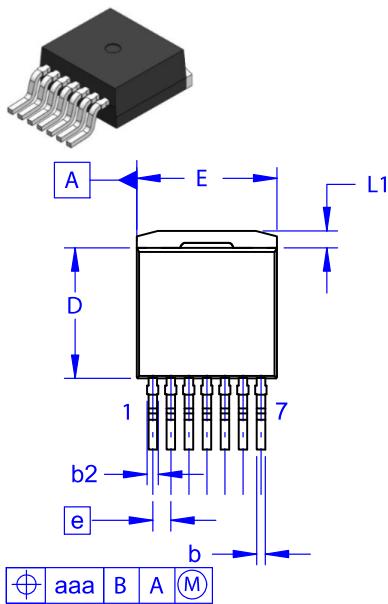


Figure 13. Junction-to-Case Transient Thermal Response Curve



D²PAK7 (TO-263-7L HV)
CASE 418BJ
ISSUE B

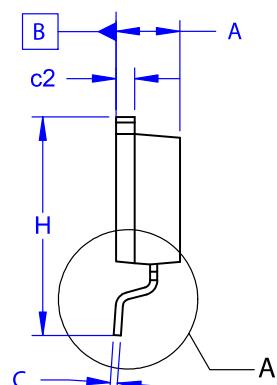
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NOTES:

- A. PACKAGE CONFORMS TO JEDEC TO-263 VARIATION CB EXCEPT WHERE NOTED.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. OUT OF JEDEC STANDARD VALUE.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	0.00	0.10	0.20
b2	0.60	0.70	0.80
b	0.51	0.60	0.70
c	0.40	0.50	0.60
c2	1.20	1.30	1.40
D	9.00	9.20	9.40
D1	6.15	6.80	7.15
E	9.70	9.90	10.20
E1	7.15	7.65	8.15
e	~	1.27	~
H	15.10	15.40	15.70
L	2.44	2.64	2.84
L1	1.00	1.20	1.40
L3	~	0.25	~
aaa	~	~	0.25

LAND PATTERN RECOMMENDATION

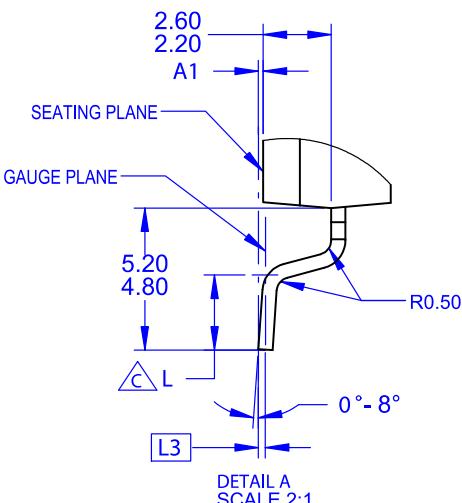


**GENERIC
MARKING DIAGRAM***



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



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